

UMZ1N Multi-Chip TRANSISTOR (NPN/PNP)**FEATURES**

Power dissipation

P_{CM}: 150 mW (T_{amb}=25°C)

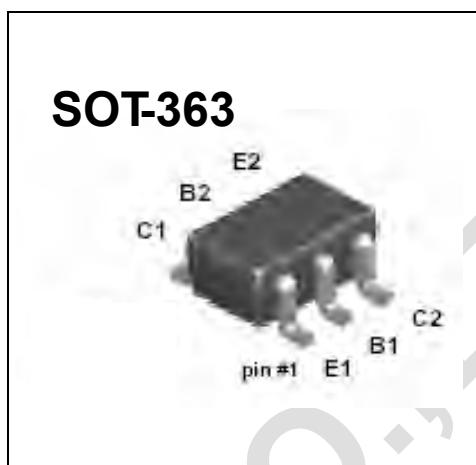
Collector current

I_{CM}: 150/-150 mA

Collector-base voltage

V_{(BR)CBO}: 60/-60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55°C to +150°C**TR1(NPN) ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =6V, I _C =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.4	V
Transition frequency	f _T	V _{CE} =12V, I _C =2mA, f=100MHz		180		MHz
Collector output capacitance	C _{ob}	V _{CB} =12V, I _E =0, f=1MHz		2	3.5	pF

TR2(PNP) ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-6V, I _C =-1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA			-0.5	V
Transition frequency	f _T	V _{CE} =-12V, I _C =2mA, f=100MHz		140		MHz
Collector output capacitance	C _{ob}	V _{CB} =-12V, I _E =0, f=1MHz		4	5	pF